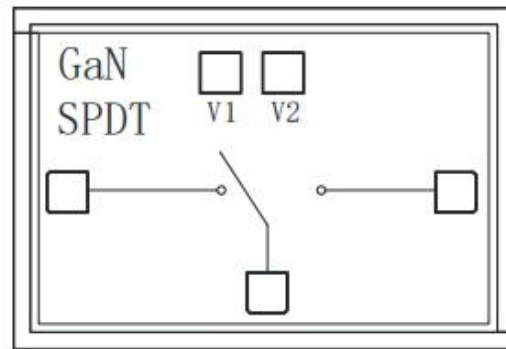


Performance

- Technology: 0.25um GaN FET
- Frequency: DC~12GHz
- Insertion loss: 1.0dB
- Isolation: 40dB
- Input P-0.3: 44dBm
- Input/Output VSWR: 1.8:1
- Switching Time: 10ns
- Control Mode: 0/-40V
- Voltage control reflective switch
- Chip size: 1.8*0.82*0.08mm

Function Diagram



Electrical Specifications (Ta=+25°C, V1~V2=0V/-40V, F=DC~12GHz)

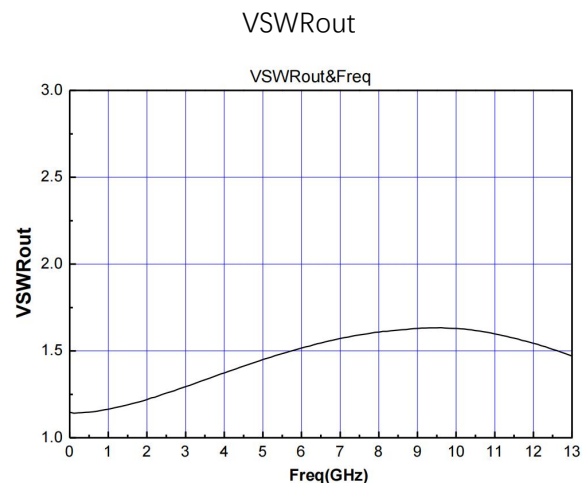
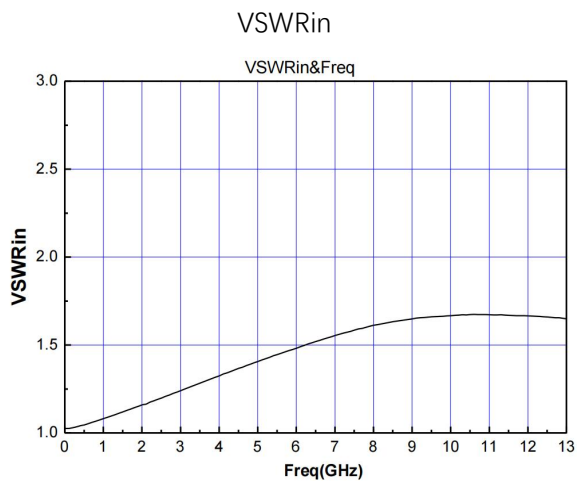
Symbol	Parameter	Min.	Typ.	Max.	Unit
Li	Insertion Loss	-	1	-	dB
ISO	Isolation	35	40	-	dB
VSWR	Input / Output VSWR	-	1.8	-	-

Absolute Maximum Ratings (Ta=+25°C)

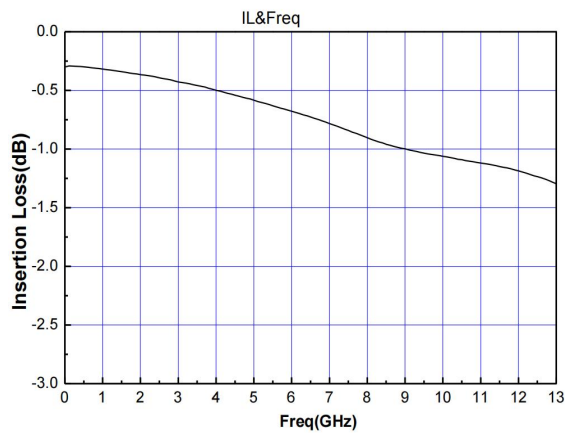
Symbol	Parameter	Value	Notes
V1,2	Control Voltage	-60V	
P _{cw}	Input Continuous Wave Power	45dBm	
T _{ch}	Channel Temperature	150°C	
T	Sintering Temperature	300°C	1min, N2 protection
T _{stg}	Storage Temperature	-55~150°C	

Exceed any of above listed ratings may cause permanent damage.

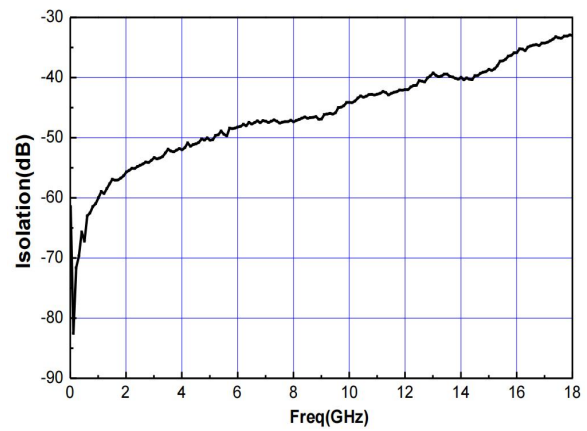
Test Curves (Ta=+25°C, (V_{1,2}=-40V))



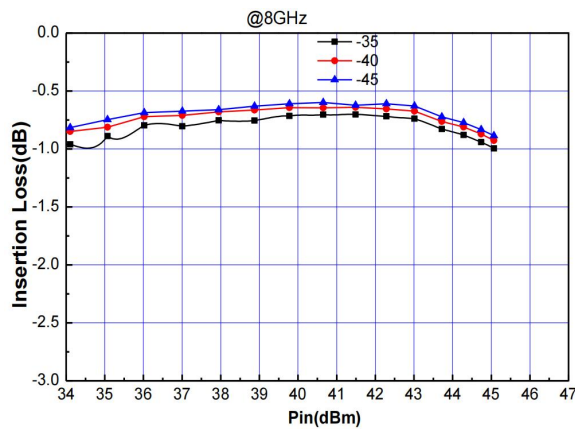
Insertion Loss



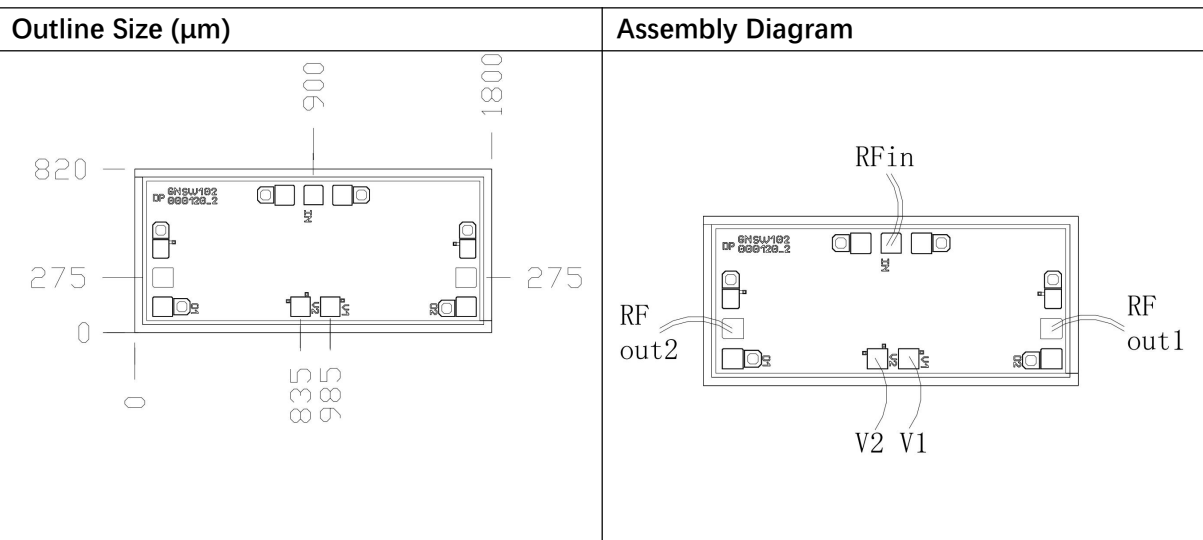
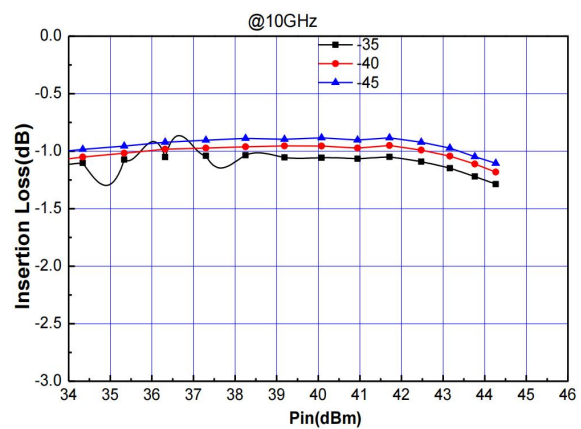
Isolation

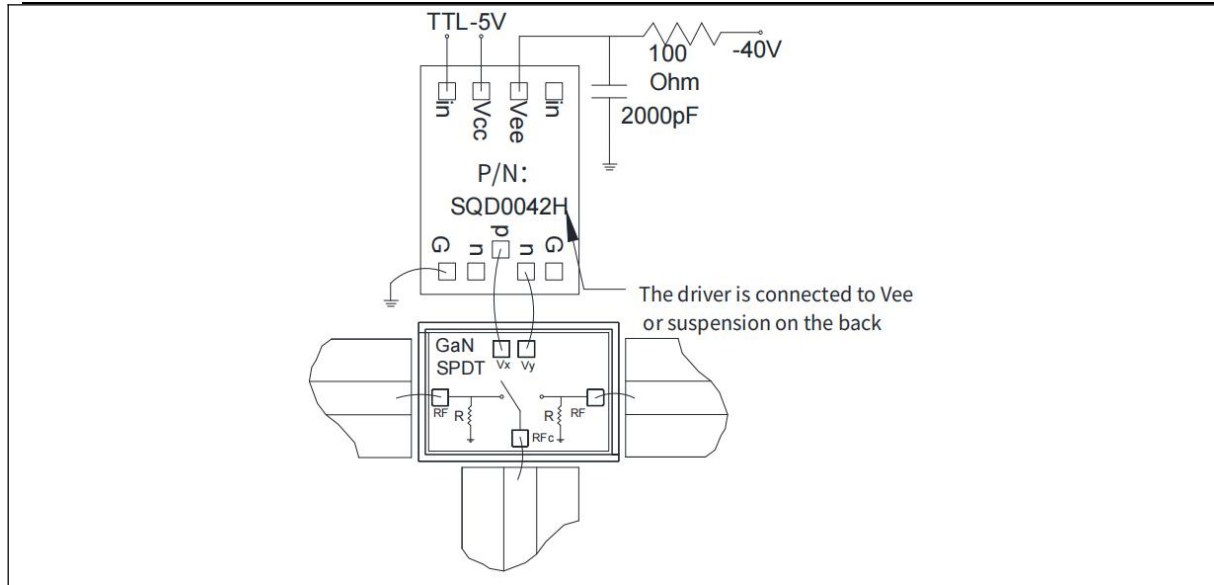


Insertion Loss@8GHz



Insertion Loss@10GHz





Truth Table

V1	V2	RFin→RFout1	RFin→RFout2
-40V	0V	ON	OFF
0V	-40V	OFF	ON